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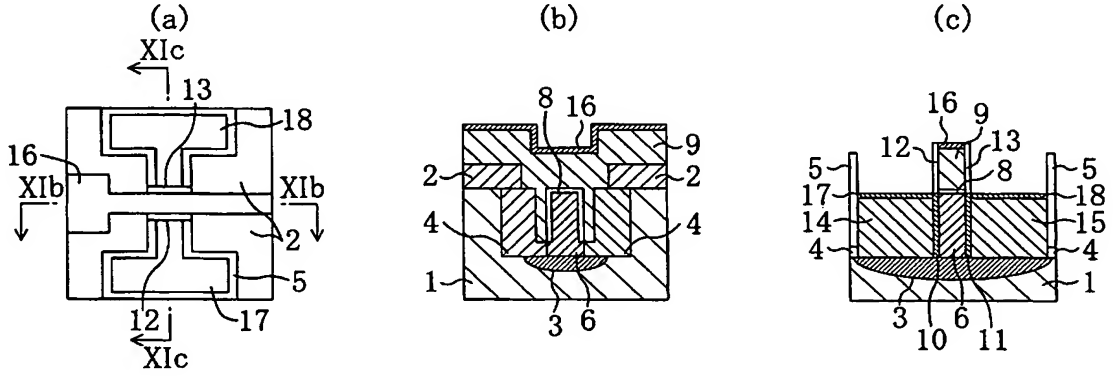
(54) Title: FINFET-TYPE SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME



(57) Abstract: A semiconductor device includes: a semiconductor substrate in which a trench is formed; a source region and a drain region each of which is buried in the trench and contains an impurity of the same conductive type; a semiconductor FIN buried in the trench and provided between the source and drain regions; a gate insulating film provided on a side surface of the semiconductor FIN as well as the upper surface of the semiconductor FIN; and a gate electrode formed on the gate insulating film.

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